F Series

Heavy-Ion Partially Depleted Silicon Surface Barrier Detectors

Main Application: Heavy-Ion spectroscopy.

Supplied with B Mount unless otherwise specified.

Active Area (mm^2)		Max Noise (keV)	≥60 µm Partially Depleted Model No.
100		18	F-018-100-60
300		23	F-023-300-60
400		28	F-028-400-60
600		33	F-033-600-60
900		35	F-035-900-60

* All standard heavy-ion detectors are cut off-axis from the parent crystal at a specific angle that will minimize channeling. Supplied in B Mount unless specified otherwise by the appropriate letter prefix.

** Greater depths on special order.

† Maximum field strength ≥15 kV/cm.

Mounting Arrangements

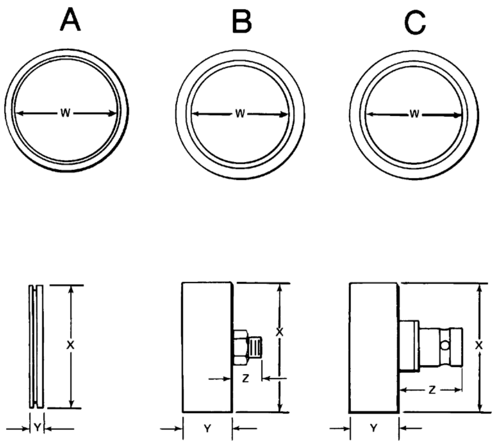
A This is a "ring mount"; i.e., the silicon wafer is offered on its ring without output connectors. This infrequently used arrangement is available on special request.

B Microdot connector on the rear of the can.

C BNC connector on the rear of the can.

Dimensions are given in millimeters.

Detector Size (mm^2)	W (Nominal)	Type A Mount		Type B Rear Microdot			Type C Rear BNC		
		X	Y	X	Y	Z	X	Y	Z
100	11.3	22.0	3.7	23.6	12.3	7.1	23.6	12.3	15.9
300	19.5	27.1	3.7	28.6	12.3	7.1	28.6	12.3	15.9
400	22.6	30.5	3.7	32.0	12.3	7.1	32.0	12.3	15.9
600	27.6	34.1	3.7	36.1	12.3	7.1	36.1	12.3	15.9
900	33.9	43.2	3.7	45.2	12.3	7.1	45.2	12.3	15.9
Tol.	±0.5	±0.3	±0.3	±0.3	±0.3	±0.3	±0.3	±0.3	±0.3



Specifications subject to change
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